**Product data sheet** 

# 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Logic-level compatible
- Trench MOSFET technology
- Very fast switching
- AEC-Q101 qualified

# 3. Applications

- High-side loadswitch
- High-speed line driver
- Relay driver
- Switching circuits

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-	-3.5	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 25 °C		-	48	55	mΩ

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



20 V, P-channel Trench MOSFET

# 5. Pinning information

#### Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u></u> 3	D I
2	S	source		
3	D	drain	1 2	G TITLE
			TO-236AB (SOT23)	Š
				017aaa094

# 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV48XPA	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

# 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV48XPA	%DZ

[1] % = placeholder for manufacturing site code

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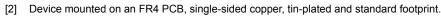
# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>amb</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-3.5	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-2.2	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-14	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	[2]	-	510	mW
			[1]	-	930	mW
		T <sub>sp</sub> = 25 °C		-	4150	mW
Tj	junction temperature			-	150	°C
T <sub>amb</sub>	ambient temperature			-55	150	°C
T <sub>stg</sub>	storage temperature			-65	150	°C
Source-drain d	liode				'	
Is	source current	T <sub>amb</sub> = 25 °C	[1]	-	-1	Α

<sup>[1]</sup> Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.



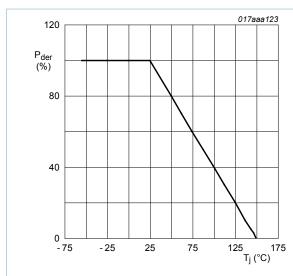


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

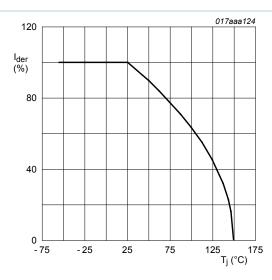


Fig. 2. Normalized continuous drain current as a function of junction temperature

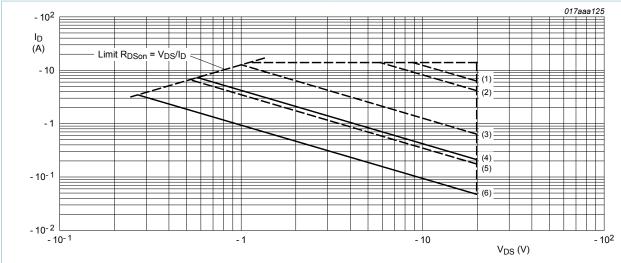
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

PMV48XPA

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### 20 V, P-channel Trench MOSFET



I<sub>DM</sub> = single pulse

- (1)  $t_p = 100 \mu s$
- (2)  $t_p = 1 \text{ ms}$
- (3)  $t_p = 10 \text{ ms}$
- (4) DC;  $T_{sp}$  = 25 °C
- $(5) t_p = 100 ms$
- (6) DC;  $T_{amb}$  = 25 °C; drain mounting pad 6 cm<sup>2</sup>

Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

## 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient		[1]	-	213	245	K/W
			[2]	-	117	135	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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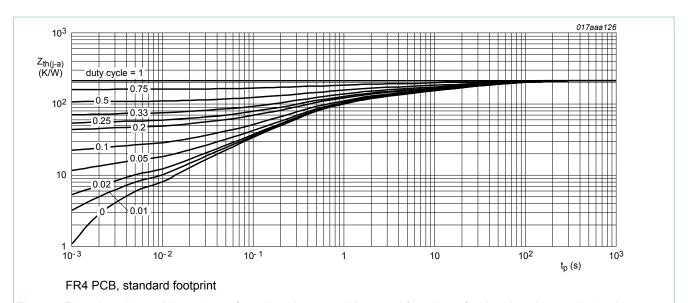


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

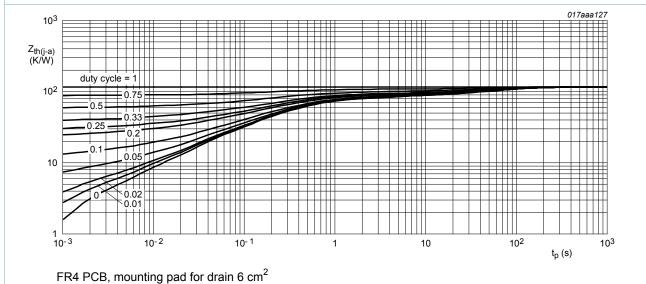


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

20 V, P-channel Trench MOSFET

# 10. Characteristics

#### Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics					
V <sub>(BR)DSS</sub>	drain-source breakdown voltage	$I_D$ = -250 $\mu$ A; $V_{GS}$ = 0 V; $T_j$ = 25 °C	-20	-	-	V
$V_{GSth}$	gate-source threshold voltage	$I_D = -250 \ \mu A; \ V_{DS} = V_{GS}; \ T_j = 25 \ ^{\circ}C$	-0.75	-1	-1.25	V
I <sub>DSS</sub>	drain leakage current	V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>amb</sub> = 25 °C	-	-	-1	μΑ
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 25 °C	-	48	55	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.4 A; $T_j$ = 150 °C	-	70	80	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -2 A; $T_j$ = 25 °C	-	71	81	mΩ
9 <sub>fs</sub>	forward transconductance	$V_{DS}$ = -12 V; $I_{D}$ = -2 A; $T_{j}$ = 25 °C	-	12	-	S
Dynamic ch	naracteristics					
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	8.5	11	nC
Q <sub>GS</sub>	gate-source charge	T <sub>j</sub> = 25 °C	-	1.8	-	nC
$Q_{GD}$	gate-drain charge		-	1.8	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -10 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	1000	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	130	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	90	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -10 V; $I_{D}$ = -1 A; $V_{GS}$ = -4.5 V;	-	11	-	ns
t <sub>r</sub>	rise time	$R_{G(ext)} = 6 \Omega$ ; $T_j = 25 °C$	-	13	-	ns
$t_{d(off)}$	turn-off delay time		-	61	-	ns
t <sub>f</sub>	fall time		-	23	-	ns
Source-dra	in diode		l			
V <sub>SD</sub>	source-drain voltage	$I_S = -2.4 \text{ A}; V_{GS} = 0 \text{ V}; T_i = 25 ^{\circ}\text{C}$	-	-0.82	-1.2	V

### 20 V, P-channel Trench MOSFET

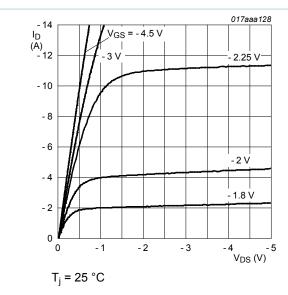
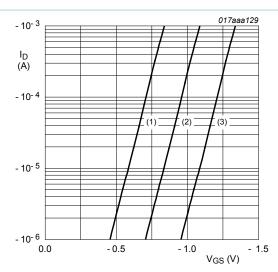


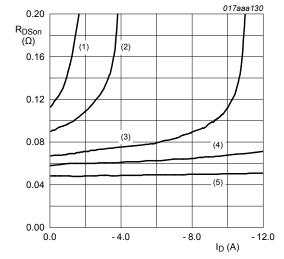
Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values



$$T_i = 25 \,^{\circ}\text{C}; \, V_{DS} = -3 \,^{\circ}\text{V}$$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 7. Sub-threshold drain current as a function of gate-source voltage



$$T_i = 25 \,^{\circ}C$$

$$(1) V_{GS} = -1.8 V$$

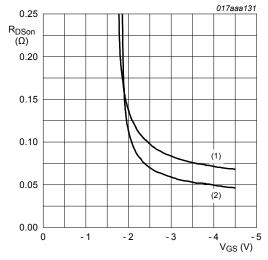
(2) 
$$V_{GS} = -2.0 \text{ V}$$

$$(3) V_{GS} = -2.25 V$$

$$(4) V_{GS} = -3.0 V$$

$$(5) V_{GS} = -4.5 V$$

Fig. 8. Drain-source on-state resistance as a function of drain current; typical values



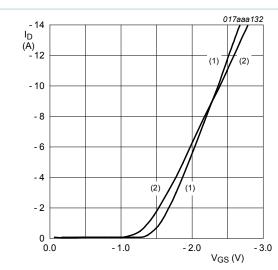
$$I_D = -2.4 A$$

(1) 
$$T_i = 125 \, ^{\circ}C$$

(2) 
$$T_i = 25 \, ^{\circ}C$$

Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

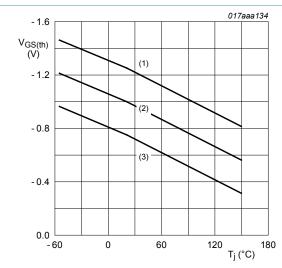
### 20 V, P-channel Trench MOSFET



$$V_{DS} > I_D \times R_{DSon}$$
  
(1)  $T_i = 25 \, ^{\circ}C$ 

(2) 
$$T_i = 150 \,^{\circ}\text{C}$$

Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values



 $I_D$  = -0.25 mA;  $V_{DS}$  =  $V_{GS}$ 

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 12. Gate-source threshold voltage as a function of junction temperature

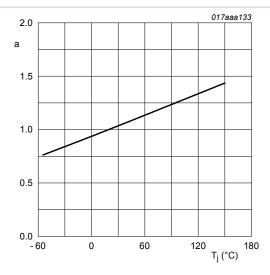
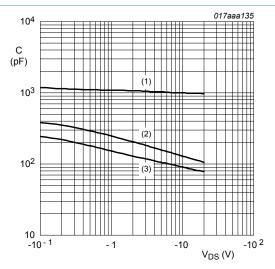


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $f = 1 MHz; V_{GS} = 0 V$ 

- (1) C<sub>iss</sub>
- (2) C<sub>oss</sub>
- (3) C<sub>rss</sub>

Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

### 20 V, P-channel Trench MOSFET

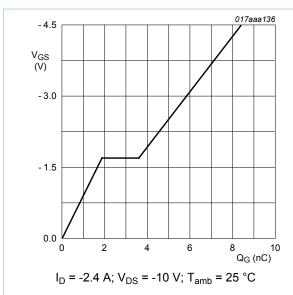


Fig. 14. Gate-source voltage as a function of gate charge; typical values

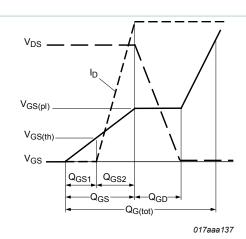
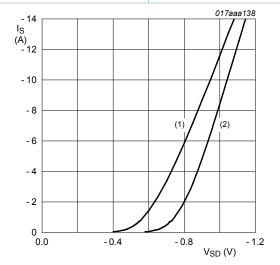


Fig. 15. Gate charge waveform definitions



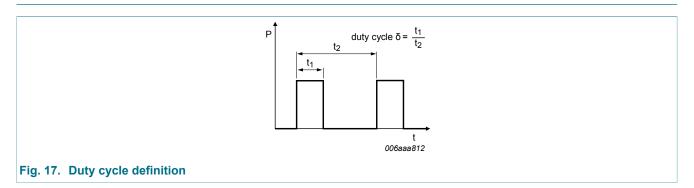
 $V_{GS} = 0 V$ (1)  $T_j = 150 \,^{\circ}C$ 

(2)  $T_i = 25 \,^{\circ}\text{C}$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

20 V, P-channel Trench MOSFET

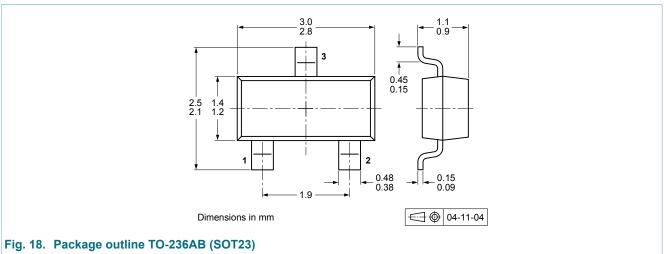
# 11. Test information



## 11.1 Quality information

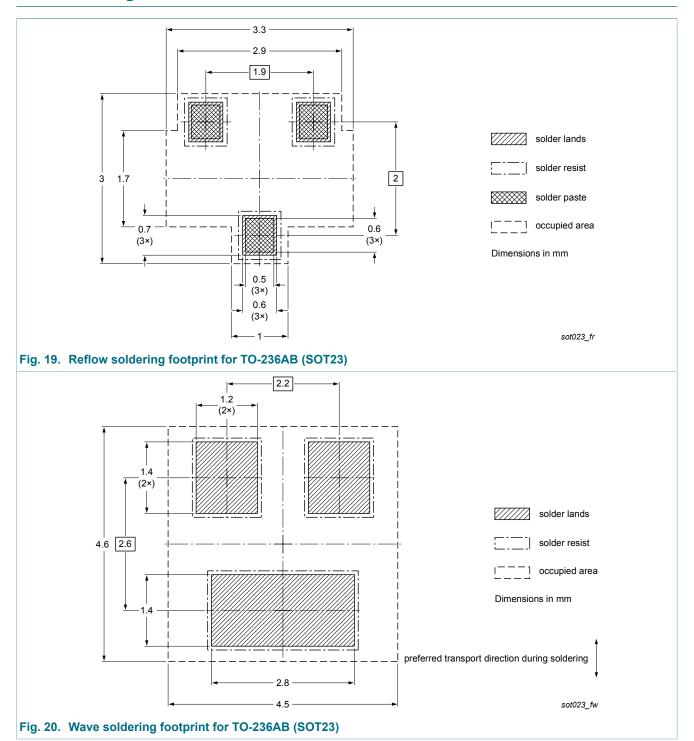
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - Stress test qualification for discrete semiconductors, and is suitable for use in automotive applications.

# 12. Package outline



20 V, P-channel Trench MOSFET

# 13. Soldering



20 V, P-channel Trench MOSFET

# 14. Revision history

### Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PMV48XPA v.1	20140310	Product data sheet	-	-

12/15

#### 20 V, P-channel Trench MOSFET

## 15. Legal information

#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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PMV48XPA

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20 V, P-channel Trench MOSFET

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## 20 V, P-channel Trench MOSFET

# 16. Contents

1	General description	1
2	Features and benefits	1
3	Applications	1
4	Quick reference data	1
5	Pinning information	2
6	Ordering information	2
7	Marking	2
8	Limiting values	3
9	Thermal characteristics	4
10	Characteristics	6
11	Test information	10
11.1	Quality information	10
12	Package outline	10
13	Soldering	11
14	Revision history	12
15	Legal information	13
15.1	Data sheet status	13
15.2	Definitions	13
15.3	Disclaimers	13
15.4	Trademarks	14

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